

20V Dual P-Channel MOSFET



SOP-8

Pin Definition:

1. Source 1 8. Drain 1 2. Gate 1 7. Drain 1 3. Source 2 6. Drain 2 4. Gate 2 5. Drain 2

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(m\Omega)$	I _D (A)
-20	40 @ V _{GS} = -4.5V	-6.4
	60 @ V _{GS} = -2.5V	-5.1

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

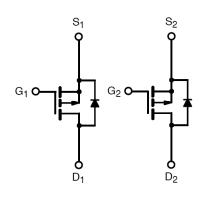
Application

- Load Switch
- PA Switch

Ordering Information

Part No.	Package	Packing
TSM9434DCS RL	SOP-8	2.5Kpcs / 13" Reel

Block Diagram



Dual P-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V_{DS}	-20	V	
Gate-Source Voltage		V_{GS}	±8	V	
Continuous Drain Current		I _D	-6.4	А	
Pulsed Drain Current		I _{DM}	±10	А	
Continuous Source Current (Diode C	Conduction) ^{a,b}	I _S	-2.5	А	
Maximum Power Dissipation	Ta = 25°C	- P _D	2.5	W	
	Ta = 70°C		1.6		
Operating Junction Temperature	·	TJ	+150	°C	
Operating Junction and Storage Tem	nperature Range	T _J , T _{STG} - 55 to +150		°C	

Thermal Performance

Parameter	Symbol	Limit	Unit			
Junction to Case Thermal Resistance	R⊖ _{JC}	30	°C/W			
Junction to Ambient Thermal Resistance (PCB mounted)	RΘ _{JA}	50	°C/W			

Notes:

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature



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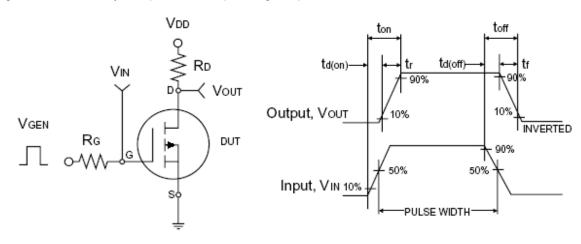


Electrical Specifications

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static				•		
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = -250uA$	BV _{DSS}	-20			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250uA$	$V_{GS(TH)}$	-0.4		-1.0	V
Zero Gate Voltage Drain Current	$V_{DS} = -16V, V_{GS} = 0V$	I _{DSS}			-1.0	uA
Gate Body Leakage	$V_{GS} = \pm 8V, V_{DS} = 0V$	I _{GSS}	1		±100	nA
On-State Drain Current	V _{DS} ≤-5V, V _{GS} = -4.5V	I _{D(ON)}	-10			Α
Drain-Source On-State Resistance	$V_{GS} = -4.5V$, $I_D = -6.4A$	0		31	40	mΩ
Dialii-Source Oil-State Resistance	$V_{GS} = -2.5V$, $I_D = -5.1A$	$R_{DS(ON)}$	-	45	60	
Forward Transconductance	$V_{DS} = -9V, I_{D} = -6.4A$	9 _{fs}		14		S
Diode Forward Voltage	I _S = -2.5A, V _{GS} = 0V	V_{SD}		- 0.9	-1.2	V
Dynamic ^b						
Total Gate Charge	$V_{DS} = -10V$, $V_{DS} = -6.4A$, $V_{GS} = -4.5V$	Q_g		12.5	19	
Gate-Source Charge		Q_gs		1.7		nC
Gate-Drain Charge	V _{GS} = -4.5 V	Q_{gd}	-	3.3		
Input Capacitance	\/ - 40\/ \/ - 0\/	C _{iss}	-	1020		
Output Capacitance	$V_{DS} = -10V, V_{GS} = 0V,$	C_{oss}	1	191		pF
Reverse Transfer Capacitance	f = 1.0MHz	C_{rss}		140		
Switching ^c						
Turn-On Delay Time	V - 40V D - 400	t _{d(on)}		25	40	
Turn-On Rise Time	$V_{DD} = -10V, R_L = 10\Omega,$	t _r		43	65	nS
Turn-Off Delay Time	$I_D = -1A$, $V_{GEN} = -4.5V$, $R_G = 6\Omega$	t _{d(off)}		71	110	110
Turn-Off Fall Time	1/G = 077	t _f		48	75	

Notes:

- a. pulse test: PW ≤300µS, duty cycle ≤2%
- b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



Switching Test Circuit

Switchin Waveforms

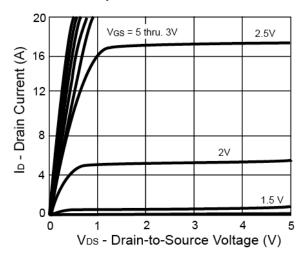


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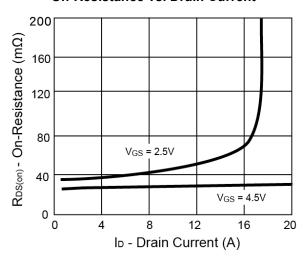


Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

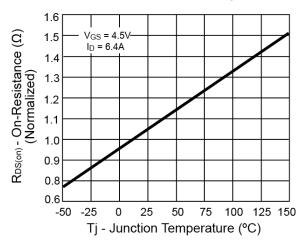
Output Characteristics



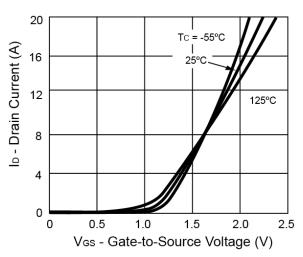
On-Resistance vs. Drain Current



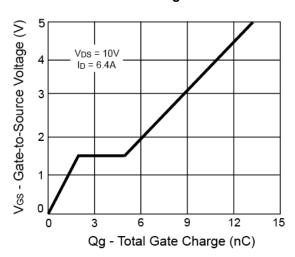
On-Resistance vs. Junction Temperature



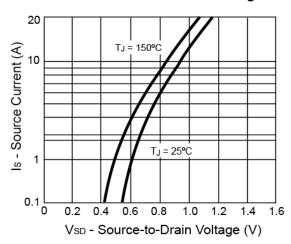
Transfer Characteristics



Gate Charge



Source-Drain Diode Forward Voltage



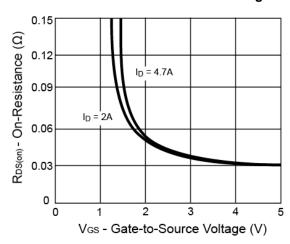


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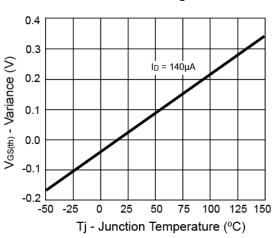


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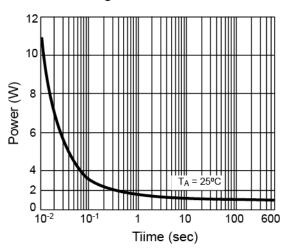
On-Resistance vs. Gate-Source Voltage



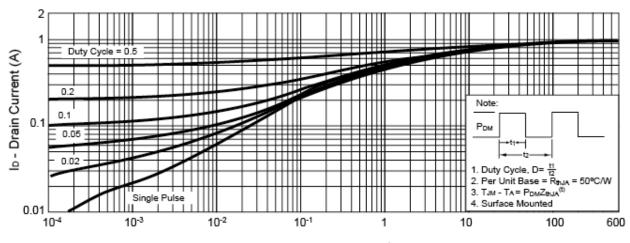
Threshold Voltage



Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient



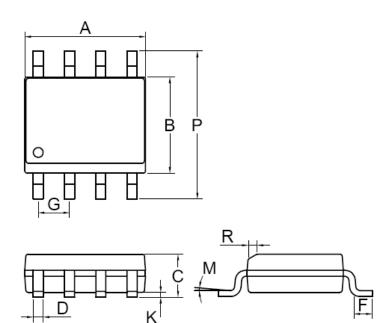
Square Wave Pulse Duration (sec)



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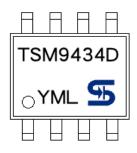


SOP-8 Mechanical Drawing



SOP-8 DIMENSION					
DIM	MILLIMETERS		INCHES		
	MIN	MAX	MIN	MAX.	
Α	4.80	5.00	0.189	0.196	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.05	BSC	
K	0.10	0.25	0.004	0.009	
М	0°	7°	0°	7°	
Р	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

Marking Diagram



Y = Year Code

M = Month Code

(A=Jan, B=Feb, C=Mar, D=Apl, E=May, F=Jun, G=Jul, H=Aug,

I=Sep, J=Oct, K=Nov, L=Dec)

5/6

L = Lot Code

Version: B07



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